60 P □ □ □

□ □ □ □ □ □ □ □□ □ □ □ □ □ □ □ □□ □□ □ T_A= 25℃ unless otherwise specified

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250uA	-60	---	---	V
$\triangle BV_{DSS}/\triangle T_J$	BV_{DSS} Temperature Coefficient	Reference to 25℃ , I_D=-1mA	---	-0.05	---	
I_{DSS}	Drain-Source Leakage Current		---	---	-1	uA
			---	---	-10	uA
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V , V_{DS}=0V	---	---	±100	nA

On Characteristics

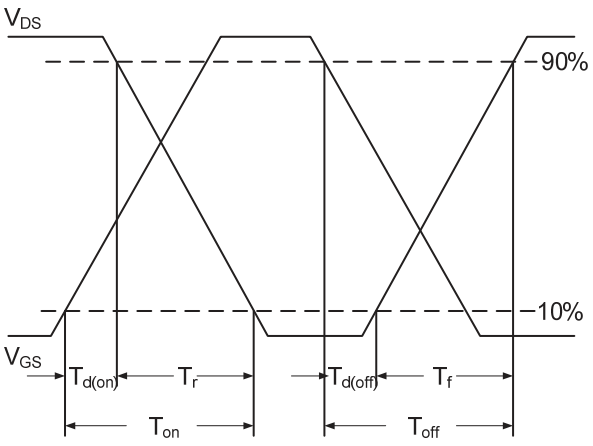
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-10V , I_D=-2A	---	160	190	m
		V_{GS}=-4.5V , I_D=-1.5A	---	200	240	m
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=-250uA	-1.2	-1.9	-2.5	V
$\triangle V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	5	---	
gfs	Forward Transconductance	V_{DS}=-10V , I_D=-2A	---	3.5	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge[2,3]	V_{DS}=-30V , V_{GS}=-10V , I_D=-2A	---	8.2	12	nC
Q_{gs}	Gate-Source Charge[2,3]		---	1.8	3.6	
Q_{gd}	Gate-Drain Charge[2,3]		---	1.5	3	
$T_{d(on)}$	Turn-On Delay Time[2,3]	V_{DD}=-30V , V_{GS}=-10V , R_G=6				

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width Ú 300us , duty cycle Ú 2 % .
3. Essentially independent of operating temperature.


VDS
90%
10%
VGS
Td(on)
Tr
Td(off)
Tf
Ton
Toff

-BVDSS
BVDSS-(-VDD)
-BVDSS
-VDD
-IAS
-VGS